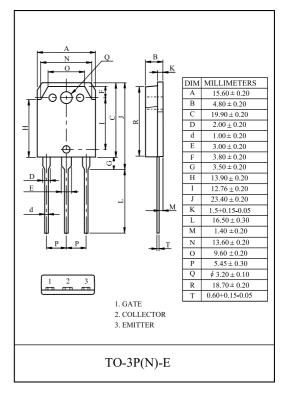
General Description

Din-Tek Field Stop Trench IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching application such as IH(induction heating), microwave oven, etc.

FEATURES

- · High speed switching
- · High ruggedness, temperature stable behavior
- · Soft current turn-off waveforms
- · Extremely enhanced avalanche capability



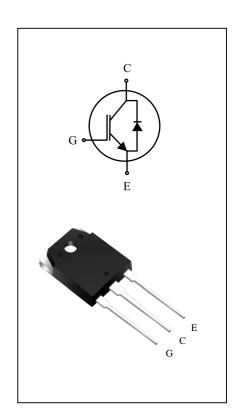
MAXIMUM RATING (Ta=25)

CHARACTERISTIC		SYMBOL RATING		UNIT
Collector-Emitter Voltage		V _{CES}	1350	V
Gate-Emitter Voltage		V _{GES}	± 20	V
Collector Current	@Tc=25	- I _C	50	A
Conector Current	@Tc=100	10	25	A
Pulsed Collector Current		I _{CM} *	75	A
Diode Continuous Forward Current	@Tc=100	I_{F}	25	A
Diode Maximum Forward Current		I_{FM}	75	A
Maximum Power Dissipation	@Tc=25	- P _D	250	W
Waxiiidiii I owel Dissipation	@Tc=100	1 1 1	100	W
Maximum Junction Temperature		T _j	150	
Storage Temperature Range		T_{stg}	-55 to + 150	

^{*}Repetitive rating: Pulse width limited by max. junction temperature

THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R _{thJC}	0.5	/W
Thermal Resistance, Junction to Case (DIODE)	R _{thJC}	2.0	/W
Thermal Resistance, Junction to Ambient	R _{th JA}	40	/W





ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static				ı		
Collector-Emitter Breakdown Voltage	BV _{CES}	V _{GE} =0V , I _C =1mA	1350	-	-	V
Collector Cut-off Current	I _{CES}	V _{GE} =0V, V _{CE} =1350V	-	-	1.0	mA
Gate Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$	-	-	± 100	nA
Gate Threshold Voltage	V _{GE(th)}	$V_{GE}=V_{CE}$, $I_{C}=25$ mA	5.0	6.0	7.5	V
	77	V_{GE} =15V, I_{C} =20A	-	1.7	-	V
Collector Emittor Seturation Voltage		V _{GE} =15V, I _C =25A	-	1.8	2.1	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V_{GE} =15V, I_{C} =25A, T_{C} = 125	-	1.95	-	V
		V _{GE} =15V, I _C =50A	-	2.2	-	V
Dynamic	,					
Total Gate Charge	Q_{g}		-	280	-	nC
Gate-Emitter Charge	Q_{ge}	V_{CC} =600V, V_{GE} =15V, I_{C} = 25A	-	35	-	nC
Gate-Collector Charge	Q_{gc}		-	145	-	nC
Turn-On Delay Time	t _{d(on)}		-	50	-	ns
Rise Time	t _r		-	20	-	ns
Turn-Off Delay Time	t _{d(off)}	V 600V L 25 L V 15V D 10	-	320	-	ns
Fall Time	$t_{\rm f}$	V_{CC} =600V, I_{C} =25A, V_{GE} =15V, R_{G} =10 Inductive Load, T_{C} = 25	-	110	-	ns
Turn-On Switching Loss	E _{on}		-	3.6	-	mJ
Turn-Off Switching Loss	E _{off}		-	1.1	-	mJ
Total Switching Loss	E _{ts}		-	4.7	-	mJ
Turn-On Delay Time	t _{d(on)}		-	55	-	ns
Rise Time	t _r		-	25	-	ns
Turn-Off Delay Time	t _{d(off)}	V_{CC} =600V, I_{C} =25A, V_{GE} =15V, R_{G} =10 Inductive Load, T_{C} = 125	-	335	-	ns
Fall Time	t _f		-	220	-	ns
Turn-On Switching Loss	E _{on}		-	3.7	-	mJ
Turn-Off Switching Loss	E _{off}		-	2.0	-	mJ
Total Switching Loss	E _{ts}		-	5.7	-	mJ
Input Capacitance	C _{ies}		-	4300	-	pF
Ouput Capacitance	C _{oes}	V _{CE} =30V, V _{GE} =0V, f=1MHz	-	110	-	pF
Reverse Transfer Capacitance	C _{res}		-	75	-	pF



ELECTRICAL CHARACTERISTIC OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V_{F}	$I_F = 25A$	T _C =25	-	1.9	2.5	V
			T _C =125	-	2.0	-	
Diode Reverse Recovery Time	t _{rr}		T _C =25	-	220	290	ns
Diode Reverse Recovery Time		I_F = 25A di/dt = 200A/ μ s	T _C =125	-	250	-	115
Diode Peak Reverse Recovery Current	I_{rr}		T _C =25	-	30	39	A
			T _C =125	-	39	-	A
Diode Reverse Recovery Charge	Q_{rr}		T _C =25	-	3400	4420	nC
	Vrr		T _C =125	-	4900	-	iiC



Fig 1. Saturation Voltage Characteristics

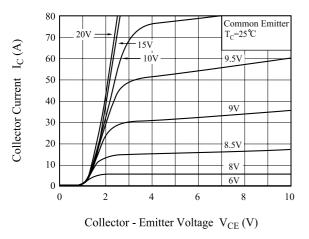


Fig 3. Saturation Voltage vs. Case Temperature

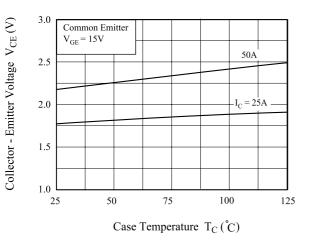


Fig 5. Saturation Voltage vs. V_{GE}

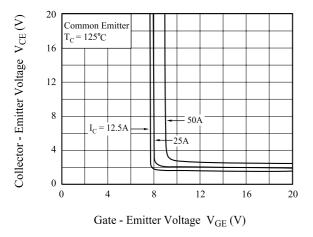


Fig 2. Saturation Voltage Characteristics

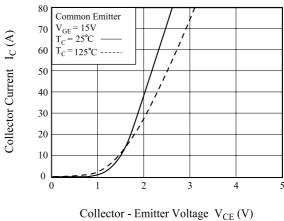


Fig 4. Saturation Voltage vs. V_{GE}

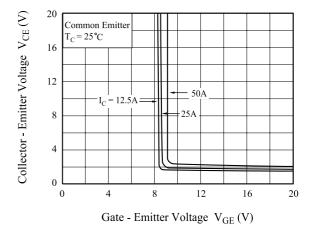
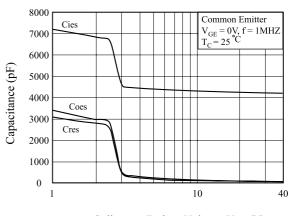


Fig 6. Capacitance Characteristics



Collector - Emitter Voltage $V_{CE}(V)$



Fig 7. Turn-On Characteristics vs. Gate Resistance

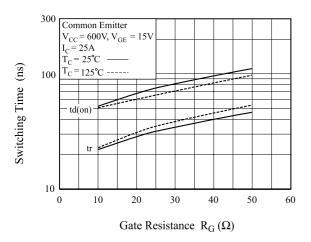


Fig 8. Turn-Off Characteristics vs. Gate Resistance

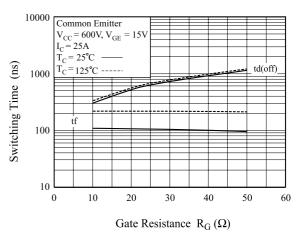


Fig 9. Switching Loss vs. Gate Resistance

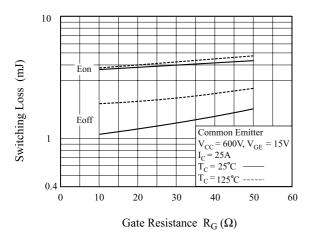


Fig 10. Turn-On Characteristics vs. Collector Current

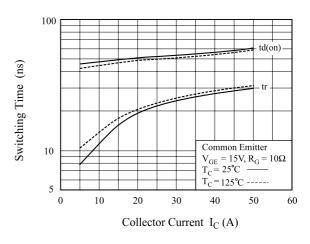


Fig 11. Turn-Off Characteristics vs. Collector Current

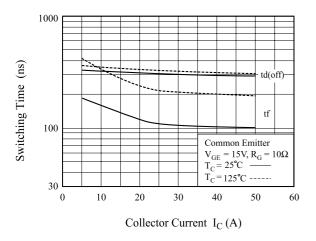


Fig 12. Switching Loss vs. Collector Current

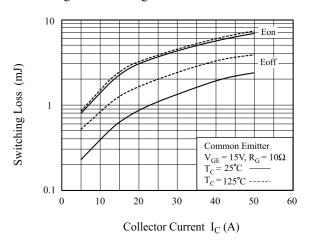




Fig 13. Gate Charge Characteristics

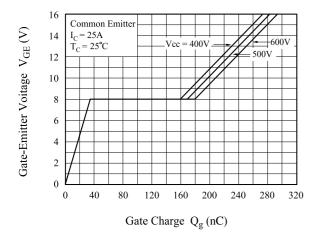


Fig 14. SOA Characteristics

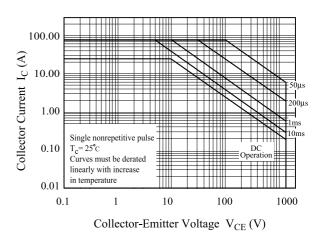


Fig 15. Turn-Off SOA

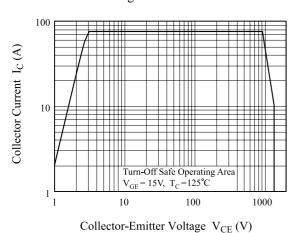
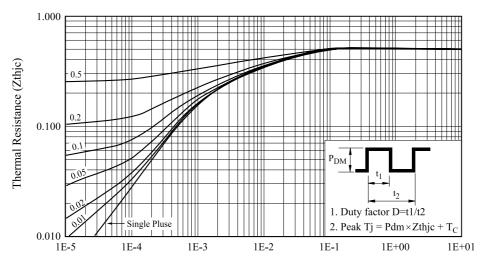


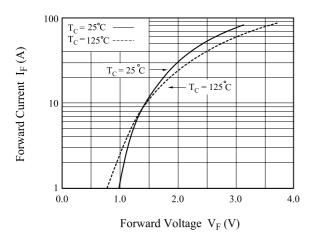
Fig 16. Transient Thermal Impedance of IGBT



Rectangular Pulse Duration (sec)



Fig 17. Forward Characteristics



Reverse Recovery Current IRRM (A) 45 40 35 $di/dt=200A/\mu s$ 30 25 20 $di/dt = 100 A/\mu s$ 15 10 0 0 10 20 30 40 50

Forward Current I_F (A)

Fig 18. Reverse Recovery Current

Fig 19. Reverse Recovery Time

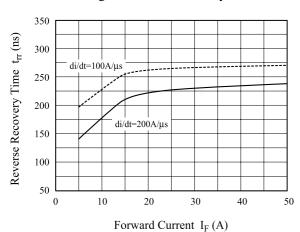




Fig 20. Switching Test Circuit

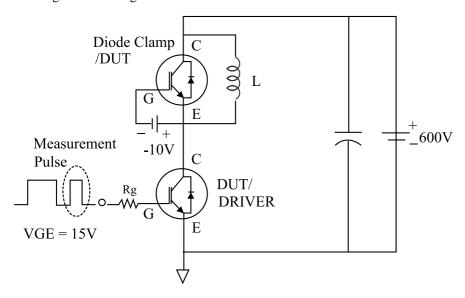
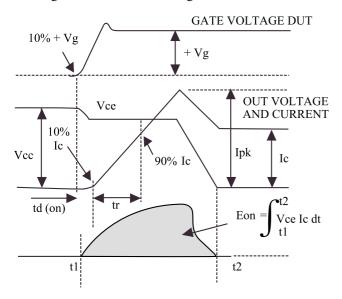


Fig 21. Definition Switching Time & Loss



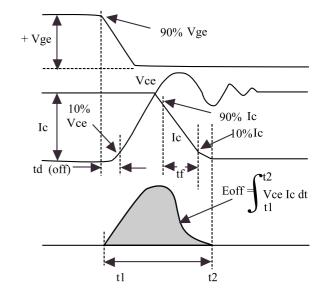
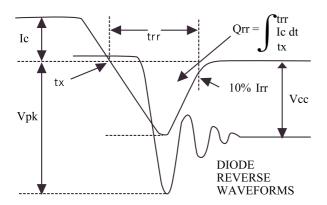
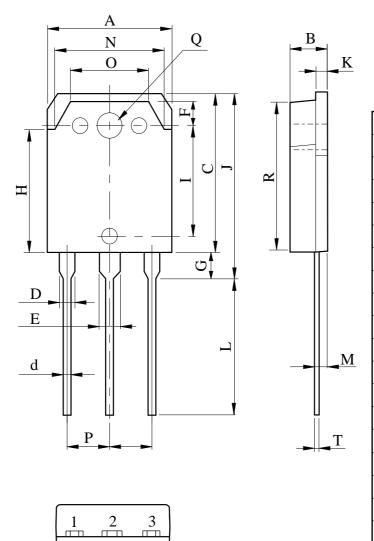


Fig 22. Definition Diode Switching Time





TO-3P (High Voltage)



DIM	MILLIMETERS
A	15.60 ± 0.20
В	4.80 ± 0.20
С	19.90 ± 0.20
D	2.00 ± 0.20
d	1.00 ± 0.20
Е	3.00 ± 0.20
F	3.80 ± 0.20
G	3.50 ± 0.20
Н	13.90 ± 0.20
I	12.76 ± 0.20
J	23.40 ± 0.20
K	1.5+0.15-0.05
L	16.50 ± 0.30
M	1.40 ± 0.20
О	9.60 ± 0.20
P	5.45 ± 0.30
Q	$\phi 3.20 \pm 0.10$
R	18.70 ± 0.20
Т	0.60+0.15-0.05





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